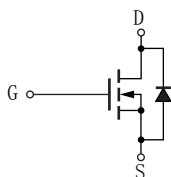


N-Channel MOSFET

2SK3269-ZJ

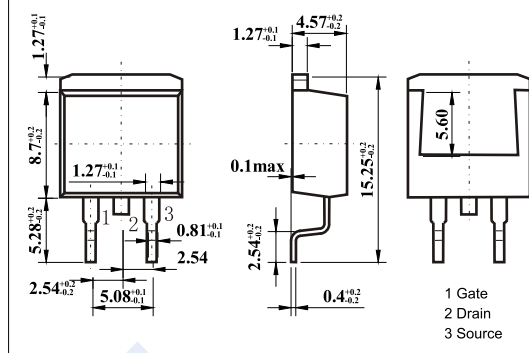
■ Features

- $V_{DS} (V) = 100V$
- $I_D = 25 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 100m\Omega$ ($V_{GS} = 10V$)
- Low on-resistance, Low Q_g
- High avalanche resistance



TO-263

Unit: mm



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	25	A
Pulsed Drain Current	I_{DM}	100	
Power Dissipation	P_D	40	W
		1.4	
Single Avalanche Energy (Note.1)	E_{AS}	22.5	mJ
Thermal Resistance.Junction- to-Ambient	R_{thJA}	89.3	$^\circ C/W$
Thermal Resistance.Junction- to-Case	R_{thJC}	3.125	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=1mA, V_{GS}=0V$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$			10	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=10V, I_D=1mA$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=12A$			100	$m\Omega$
Forward Transconductance	g_{FS}	$V_{GS}=10V, I_D=12A$	6	11		S
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=10V, f=1MHz$		960		pF
Output Capacitance	C_{oss}			285		
Reverse Transfer Capacitance	C_{rss}			85		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=30V, I_D=12A, R_G=2.5\Omega$		15		ns
Turn-On Rise Time	t_r			10		
Turn-Off DelayTime	$t_{d(off)}$			65		
Turn-Off Fall Time	t_f			35		
Diode Forward Voltage	V_{SD}	$I_S=15A, V_{GS}=0V$			1.4	V

N-Channel MOSFET

2SK3269-ZJ

■ Typical Characteristics

